

Nano Science and Nano Technology

Trade Science Inc.

An Indian Journal

📼 Full Paper

NSNTAIJ, 3(2), 2009 [53-57]

Raman spectroscopic studies on pulsed laser deposited nanostructured LiCoO, thin film cathodes

M.C.Rao

Department of Physics, Andhra Loyola College, Vijayawada-520008, (INDIA) E-mail : raomc72@gmail.com Received: 26th September, 2009 ; Accepted: 6th October, 2009

ABSTRACT

Thin films of LiCoO₂ were prepared by pulsed laser deposition technique. Two important deposition parameters such as substrate temperature and oxygen partial pressure during the thin film deposition were controlled. The Raman data consist of a series of broad bands located between 400 and 700cm⁻¹ for LiCoO₂ films. The Raman band located at 592cm⁻¹ can be viewed as the symmetric Co-O stretching vibration of CoO₆ groups. This band is assigned to the A_{1g} symmetry. The RS peak position at 484cm⁻¹ derives from the E_g species. The symmetric motions involve Co-O stretching and O-Co-O bending vibrations. The intensity ratio increased with the increase of substrate temperature. The film deposited at 700°C in pO₂=100 mTorr, indicating that the film had no preferred orientation. © 2009 Trade Science Inc. - INDIA

KEYWORDS

LiCoO₂ thin films; PLD, Raman.

INTRODUCTION

Lithiated transition metal oxides such as $LiMO_2$ (Where M=Co, Ni, Mn etc.) have received considerable attention in recent years as high voltage positive electrode materials for use in secondary lithium batteries^[1]. Among these, the high cycling stability and high cell potential against lithium makes $LiCoO_2$ an attractive cathode material in the fabrication of all solid state rechargeable microbatteries^[2,3]. Its theoretical specific capacity and energy densities are 274mAh/g and 1070Wh/kg respectively.

The layered LiCoO_2 consists of a close packed network of oxygen ions with Li and Co ions on alternative (111) planes of the cubic rocksalt sub-lattice. The edges of CoO₆ octahedral were shared to form CoO₂ sheets

and lithium ions can move in two-dimensional directions between CoO_2 sheets. Thus the layered LiCoO₂ has an anisotropic structure and thereby electrochemical lithium insertion/extraction behaviour must depend strongly on the orientation of the microcrystallites. The growth of LiCoO₂ thin films with preferred orientation is known to be crucial. Several thin film deposition techniques such as RF sputtering^[2,4], pulsed laser deposition^[4-8], electrostatic spray deposition^[9] and chemical vapour deposition^[10] were employed for the growth of LiCoO₂ thin films. A brief literature survey reveals that it is difficult to grow stoichometric and stable c-axis oriented LiCoO₂ thin films by several physical vapour deposition methods due to many growth kinetic processes which occur in vacuum or at low oxygen partial pressures.

Full Paper

Pulsed laser deposition (PLD) has been widely recognized as a very promising, versatile and efficient method for the deposition of metal oxide thin films^[11]. When PLD is carried out in the atmosphere of a chemically reactive gas (a process known as reactive pulsed laser deposition (RPLD)), the flux of the laser ablated material interacts with the gas molecules all along the transit from the target to the collector surface. The resulting deposited layer was found to have a chemical composition substantially the same as the base or starting material. Preliminary investigations on pulsed laser deposited LiCoO₂ thin films were carried out by Julien et al.^[5]. Iriyama et al.^[6] and studied the electrochemical performance. They observed that the reactivity in singlephase region at potentials more positive than 4.0V was lower than that of randomly oriented films. Poly-crystalline layered $R\overline{3}m$ phase thin films of LiCoO₂ were grown by PLD using Nd: YAG laser by Julien et al.^[12]. This LiCoO₂ cathode active films were found to deliver a specific capacity of 195mC/cm²µm in the voltage range 2.0-4.2V. In the present study the influence of deposition parameters on the Raman studies of pulsed laser deposited LiCoO₂ thin films were reported.

EXPERIMENTAL

LiCoO₂ films were grown by pulsed laser deposition technique on silicon substrates maintained at temperatures in the range 200-700°C. LiCoO₂ target was prepared by sintering a mixture of high purity LiCoO₂ and Li₂O powders (Cerac products) with excess of Li i.e. Li/Co>1.0 by adding Li₂O. The mixture was crushed and pressed at 5 tonns.cm⁻² to make tablets of 3 mm thick and 13 mm diameter. To get quite robust targets, the tablets were sintered in air at 800°C. The typical substrates i.e. Si wafers were cleaned using HF solution. The target was rotated at 10 rotations per minute with an electric motor to avoid depletion of material at any given spot. The laser used in these experiments is the 248nm line of a KrF excimer laser (Luminics PM 882) with 10 ns pulse with a repetition rate of 10 Hz. The rectangular spot size of the laser pulse was 1×3mm and the energy 300mJ. The target substrate distance was 4cm. The deposition temperature was maintained with thermocouple and temperature controller. During the deposition pure oxygen was introduced into the deposition chamber and desired pressure was maintained with a flow controller.

The Raman spectra of LiCoO₂ films were recorded between 200 and 1000cm⁻¹ at room temperature in a quasi-backscattering configuration at a spectral resolution of 2cm⁻¹. The Raman-laser apparatus (Jobin-Yvon U1000) was equipped of holographic grating double-monochromator, an intermediate spatial filter and a computer-controlled photon-counting system. The emission from a laser (Spectra-Physics, 2020 argon-ion) with a wavelength of 514.5nm was used. The frequency stability and the accuracy of the apparatus were checked recording the Raman spectrum of silicon. To avoid sample photo-decomposition or denaturation, RS spectra were recorded using a low power density of 100W/cm².

RESULTS AND DISCUSSION

Pulsed laser deposited LiCoO₂ films are pin-hole free as revealed from optical microscopy and well adherent to the substrate surface. The thickness of LiCoO₂ films is 250 nm. The influence of oxygen partial pressure (pO_2) and deposition temperature (Ts) on the Raman studies of the films are systematically studied. The chemical compositional studies made on LiCoO₂ films revealed that a minimum of 100 mTorr oxygen partial pressure is required to grow nearly stoichiometric films.

LiCoO₂ possesses the R3m space group, D_{3d}^{5} spectroscopic symmetry. According to the results of the theoretical factor-group analysis, two modes are active in the Raman spectrum (A_{1g}& E_g) of the LiCoO₂ crystal^[13]. Figure 1(a-c) shows the unpolalized Raman scattering spectra of LiCoO₂ films deposited on silicon maintained at 300C in oxygen partial pressure pO₂=100 mTorr as a function of the target composition.

These spectra displayed the Raman active mode of the silicon wafer at 520 cm^{-1} . The experimental Raman data consist of a series of broad bands located between 400 and 700 cm⁻¹. The RS peak positions at 484 and 592 cm^{-1} of PLD LiCoO₂ films are in good agreement with those reported for the LiCoO₂ crystal^[14]. The vibrational signature of the LiCoO₂ matches well the two allowed Raman modes. The peak







M.C.Rao

Figure 2 : Raman spectra of LiCoO₂ thin films deposited at different substrate temperatures in pO₂=100 mTorr

located at 693 cm⁻¹ in Raman spectra (Figure 1(a) and (b)) indicates the presence of Co_3O_4 impurities in the film^[15]. The formation of Co_3O_4 is related to lithium loss during the deposition process. In order to compensate this loss we have prepared films from lithium rich targets including addition of 10 and 15% of Li₂O concentration. The corresponding spectra are shown in Figure 1(b-c). Upon addition of Li₂O, the peak at 693cm⁻¹ decreased substantially indicating the disappearance of Co_3O_4 species as it is shown in the RS spectra (Figure1(c)). The optimum concentration of Li₂O to compensate the lithium loss must be 15% of Li₂O. LiCoO₂ possess the prototype symmetry R-3m of the rock-salt structure, where the cobalt cations reside on the octahedral 3a sites, the lithium ions oc-

55

Full Paper

cupy the octahedral 3b interstices, and the oxygen anions are in a cubic close-packing, occupying the 6c sites^[15]. It is also convenient to analyze the RS spectrum in terms of localized vibrations, considering the rock-salt structure built of CoO₆ and LiO₆ octahedra^[14]. The Raman band located at 592cm⁻¹ can be viewed as the symmetric Co-O stretching vibration of CoO_6 groups. This band is assigned to the A_{1g} symmetry in the D_{3d}^5 spectroscopic space group. Its broadening could be related with the cation-anion bond lengths and polyhedral distortion occurring in $LiCoO_{\gamma}$. The RS peak at 484cm⁻¹ derives from the E_a species. The Raman bands are likely lie to the motions involving mainly the Co-O stretching and O-Co-O bending, as the contributions of the Raman modes are only from the motion of the oxygen atoms.

The polarized scattering spectra show uniaxially (003) textured LiCoO₂ thin films. Based on the intensity ratio of Raman spectra, the peaks situated at 484 and 592cm⁻¹ correspond to the E_g and A_{1g} optical modes of LiCoO₂, respectively^[14]. The polarization dependence of the recorded spectra is consistent with the prediction for phonon symmetries. These results show that, as expected, the A_{1g} stretching mode should be at higher energy than the E_g bending mode.

Information for the structural quality of the PLD LiCoO₂ films can be given considering the Raman data using the shape and the frequency of two peaks located in the low and high frequency region of the spectra. When the PLD films were grown from target with $Li_{2}O \le 15\%$, the oscillator strength of the $A_{1,a}$ stretching mode of RS spectra rose with a narrow full width at half maximum (FWHM). This phenomenon is due to the well-defined rock-salt structure of the films and the regular distortion of CoO₆ octahedra. As the stretching mode is sensitive to the film morphology, low FWHM values provide evidence for the rock-salt-like structure for samples grown at a high substrate temperature. These spectroscopic results indicate that the conjunction of target composition (lithium-rich), substrate temperature (T_s>300°C), and oxygen partial pressure (pO₂-100 mTorr) promotes reconstruction of the stoichiometric LiCoO₂ layered framework.

Raman spectroscopy is also useful to distinguish between different symmetries in a given material. Figure 2 shows non-polarized Raman spectra of thin films deposited at different temperatures in pO₂₌100 mTorr. The spectra are nonpolarized by the intensity of the A_{1g} peak at 592cm⁻¹. I₄₈₄ and I₅₉₄ are referred as intensities of the E_g and A_{1g} bands respectively. The I₄₈₄/I₅₉₄ increased with a decrease in the degree of the c-axis orientation of the films. The film deposited at 700°C in pO₂₌100 mTorr, indicating that the film had no preferred orientation. These results are in good agreement with the results reported by Iriyama et al.^[9].

CONCLUSIONS

Thin films of LiCoO₂ were prepared by pulsed laser deposition. PLD films were found to be uniform with regard to the surface topography, thicknesses and well adherent to the substrate surface. The Raman band located at 592cm⁻¹ can be viewed as the symmetric Co-O stretching vibration of CoO₆ groups. The RS peak position at 484cm⁻¹ derives from the E_g species. The symmetric motions involve Co-O stretching and O-Co-O bending vibrations. The intensity ratio increased with the increase of substrate temperature. The film deposited at 700°C in pO₂₌100 mTorr, indicating that the film had no preferred orientation. These results suggest that the open and porous structured LiCoO₂ PLD films find potential applications as binder free electrode in the fabrication of all solid state microbatteries.

REFERENCES

- [1] T.Ohzuku; 'Lithium Batteries, New Materials, Developments and perspectives'GPistoia, 239, Elsevier, Amsterdam (1993).
- [2] B.J.Neudecker, N.J.Dudney, J.B.Bates; J.Electrochem.Soc,, 147, 517 (2000).
- [3] J.B.Bates, N.J.Dudney, B.Neudecker, A.Veda, C.D.Evans; Solid State Ionics, 135, 33 (2000).
- [4] P.J.Bouwman, B.A.Boukamp, H.J.M.Bouwmeester, P.H.L.Notten; Solid State Ionics, 152, 181 (2002).
- [5] C.Julien, E.Haro-Poniatowski, O.M.Hussain, C.V.Ramana; Ionics, 7, 165 (2001).
- [6] Y.Iriyama, T.Inabu, T.Abe, Z.Ogumi; J.Power Sources, 94, 175 (2001).
- [7] H.Xia, L.Lu, G.Ceder; J.Power Sources, 159, 1422 (2006).
- [8] S.B.Tang, M.O.Lai, L.Lu; J.Alloys and compounds, 449, 300 (2008).

🗅 Full Paper

- [9] C.H.Chen, A.A.J.Buysman, E.M.Kelder, J.Schoonman; Solid State Ionics, 80, 1 (1995).
- [10] W.G.Chai, S.G.Yoon; J.Power Sources, 125, 236 (2004).
- [11] J.C.Miller, R.F.Haglmel, JR.; 'Laser Ablation and Deposition', J.C.Miller and R.F.Haglmel, Academic Press, New York (1998).
- [12] C.Julien, M.A.Camacho-Lopez, L.Escobar-Alavcon, E.Haro-Poniatowski; Mater.Chem.Phys., 68, 210 (2001).

- [13] C.Julien; Solid State Ionics, 887, 136-137, (2000).
- [14] C.Julien, G.A.Nazri, A.Rougier; Mat. Res.Soc. Symp.Proc., 548, 79 (1999).
- [15] J.D.Perkins, M.L.Fu, D.M.Trickett, J.M.McGraw, T.F.Ciszek, P.A.Parilla, C.T.Roger, D.S.Ginley; Mat.Res.Soc.Symp.Proc., 496, 329 (1998).